REMARKS

Present Status of the Application

This is a full and timely response to the outstanding non-final Office Action mailed on June 30, 2004. The Office Action has rejected claims 12 and 20 under 35 U.S.C. 112, 2nd paragraph. The Office Action has also rejected claims 1-4, 6-8, 12-16 and 18-20 under 35 U.S.C. 102(b) as being anticipated by Doi (USP 5,632,821) and claims 1-5, 8-17 and 20 under 35 U.S.C. 103(a) as being unpatentable over Gupta (USP 5,24,375) in view of Doi (USP 5,632,821).

Claims 1-20 remain pending of which claims 12 and 20 have been amended to address the 35 U.S.C. 112, 2nd paragraph rejection and claims 1 and 13 have been amended to more accurately describe the invention. It is believed that no new matter is added by way of these amendments made to the claims or otherwise to the application.

Applicant has most respectfully considered the remarks set forth in this Office Action. Regarding the anticipation and obviousness rejections, it is however strongly believed that the cited references are deficient to adequately teach the claimed features as recited in the amended claims. The reasons that motivate the above position of the Applicant are discussed in detail hereafter, upon which reconsideration of the claims is most earnestly solicited.

Discussion of Office Action Rejections

The Office Action rejected claims 12 and 20 under 35 U.S.C. § 112, 2nd paragraph as being indefinite for failing to particularly point out and distinctly claim the subject matter which applicant regards as the invention.

Regarding the 112, 2nd paragraph rejection, Applicant has amended the claims according to the Examiner's suggestions. Reconsideration and withdrawal of the rejection are courteously requested.

The Office Action rejected claims 1-5, 8-17 and 20 under 35 U.S.C. § 102(b) as being anticipated by Doi (USP 5,632,821).

As described in detail hereinafter, Applicants respectfully submit that Doi is legally deficient for the purpose of anticipating claims 1 and 13 because Doi fails to disclose each element of the claim under consideration.

The present invention teaches in claims 1 and 13, among other things, performing a pre-deposition process on the chamber, followed by performing a discharge plasma treatment of the chamber. The pre-deposition process is performed under a substrate-free condition to isolate contaminants generated from the cleaning process. After the pre-deposition process, the present invention further teaches conducting a discharge plasma treatment to reduce the accumulated charge in the chamber.

Doi, on the other hand, teaches the cleaning process relies on an introduction of a post treatment gas into the chamber and a generation of plasma for the post treatment gas to react with and remove the remaining cleaning gas residue. First of all, contrary to the office's assertion, an introduction of a gas to react with the cleaning gas residues in the chamber so as to facilitate the removal of the cleaning gas residue can not be construed as performing a deposition process in a substrate-free condition to isolate contaminants in the chamber as in the instant case. Further, the plasma used in Doi is for the treatment gas to react with the cleaning gas residue (col. 6, ln. 6-19) and is not for reducing the accumulated charge as accomplished by the discharge plasma treatment of this invention.

For at least the above reasons that Doi fails to teach or suggest each element in the claims, Applicants respectfully assert that claims 1 and 13 patentably define over Doi.

Since claims 2-12 and 14-20 are dependent claims which further defines the invention recited in claims 1 and 13, respectively, Applicants respectfully assert that these claims also

are in condition for allowance. Thus, reconsideration and withdrawal of this rejection are respectively requested.

The Office Action rejected claims1-5, 8-17, and 20 under 35 U.S.C. § 103(a) as being unpatentable over Gupta(US 5,824,375) in view of Doi (US 5,632,821).

With regard to the rejections of claims by Gupta in view of Doi, Applicant respectfully submits that these claims patently define over the prior art for at least the same reasons as discussed above.

Similar to Doi, Gupta teaches a cleaning process by introducing a cleaning gas into the chamber to react with contaminants present within chamber, removing the gaseous reaction products and performing a desorption process to remove sorbed contaminants. There is no wherein Gupta that teaches a pre-deposition process to isolate contaminants and a discharge plasma treatment to reduce the accumulated charge in the chamber. As a matter of fact, neither Doi nor Gupta discloses or suggests any treatment being performed.

For at least these reasons, Applicants respectfully assert that Gupta in view of Doi fails to render claims 1 and 13 unpatentable. Since claims 2-12 and 14-20 re dependent claims which further define the invention recited in claims 1 and 13, respectively, Applicants respectfully assert that these claims also are in condition for allowance. reconsideration and withdrawal of this rejection are respectively requested.

CONCLUSION

For at least the foregoing reasons, it is believed that the presently pending claims 1-20 are in proper condition for allowance. If the Examiner believes that a telephone conference would expedite the examination of the above-identified patent application, the Examiner is invited to call the undersigned.

Respectfully submitted,

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